

Silicon NPN Planar RF Transistor

Electrostatic sensitive device.
Observe precautions for handling.

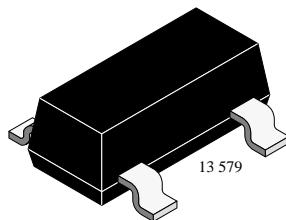
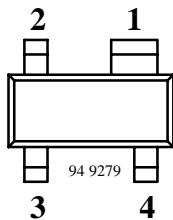


Applications

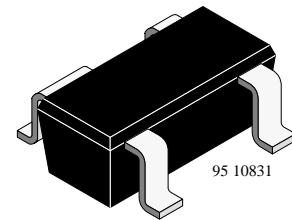
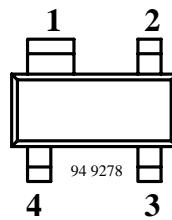
For low noise and small signal low power amplifiers. This transistor has superior noise figure and associated gain performance at UHF, VHF and microwave frequencies.

Features

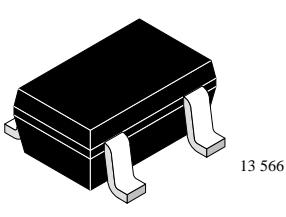
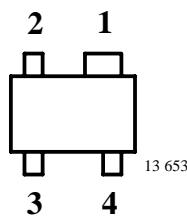
- Low power applications
- Very low noise figure
- High transition frequency $f_T = 12$ GHz



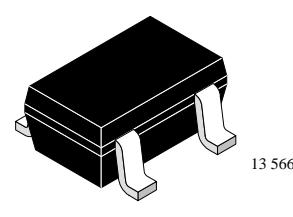
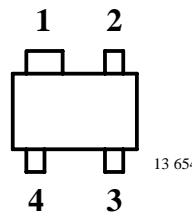
TSDF1205 Marking: F05
Plastic case (SOT 143)
1 = Collector, 2 = Emitter, 3 = Base, 4 = Emitter



TSDF1205R Marking: 05F
Plastic case (SOT 143R)
1 = Collector, 2 = Emitter, 3 = Base, 4 = Emitter



TSDF1205W Marking: WF0
Plastic case (SOT 343)
1 = Collector, 2 = Emitter, 3 = Base, 4 = Emitter



TSDF1205RW Marking: W0F
Plastic case (SOT 343R)
1 = Collector, 2 = Emitter, 3 = Base, 4 = Emitter

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Test Conditions | Symbol | Value | Unit |
|---------------------------|----------------------------------|-----------|-------------|------------------|
| Collector-base voltage | | V_{CBO} | 9 | V |
| Collector-emitter voltage | | V_{CEO} | 4 | V |
| Emitter-base voltage | | V_{EBO} | 2 | V |
| Collector current | | I_C | 12 | mA |
| Total power dissipation | $T_{amb} \leq 132^\circ\text{C}$ | P_{tot} | 40 | mW |
| Junction temperature | | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

Maximum Thermal Resistance $T_{amb} = 25^\circ C$, unless otherwise specified

| Parameter | Test Conditions | Symbol | Value | Unit |
|------------------|---|------------|-------|------|
| Junction ambient | on glass fibre printed board (25 x 20 x 1.5) mm ³ plated with 35 μ m Cu | R_{thJA} | 450 | K/W |

Electrical DC Characteristics $T_{amb} = 25^\circ C$, unless otherwise specified

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|--------------------------------------|--------------------------------|---------------|-----|-----|-----|---------|
| Collector cut-off current | $V_{CE} = 12 V$, $V_{BE} = 0$ | I_{CES} | | | 100 | μA |
| Collector-base cut-off current | $V_{CB} = 10 V$, $I_E = 0$ | I_{CBO} | | | 100 | nA |
| Emitter-base cut-off current | $V_{EB} = 1 V$, $I_C = 0$ | I_{EBO} | | | 2 | μA |
| Collector-emitter breakdown voltage | $I_C = 1 mA$, $I_B = 0$ | $V_{(BR)CEO}$ | 4 | | | V |
| Collector-emitter saturation voltage | $I_C = 5 mA$, $I_B = 0.5 mA$ | V_{CEsat} | | 0.1 | 0.5 | V |
| DC forward current transfer ratio | $V_{CE} = 2 V$, $I_C = 2 mA$ | h_{FE} | 50 | 120 | 250 | |

Electrical AC Characteristics $T_{amb} = 25^\circ C$, unless otherwise specified

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-------------------------------|---|---------------|-----|------|-----|------|
| Transition frequency | $V_{CE} = 2 V$, $I_C = 5 mA$, $f = 1 GHz$ | f_T | | 12 | | GHz |
| Collector-base capacitance | $V_{CB} = 1 V$, $f = 1 MHz$ | C_{cb} | | 0.2 | | pF |
| Collector-emitter capacitance | $V_{CE} = 1 V$, $f = 1 MHz$ | C_{ce} | | 0.35 | | pF |
| Emitter-base capacitance | $V_{EB} = 0.5 V$, $f = 1 MHz$ | C_{eb} | | 0.15 | | pF |
| Noise figure | $V_{CE} = 2 V$, $I_C = 2 mA$, $Z_S = Z_{Sopt}$, $Z_L = 50 \Omega$, $f = 2 GHz$ | F | | 1.3 | | dB |
| Power gain | $V_{CE} = 2 V$, $I_C = 2 mA$, $f = 2 GHz$ (@ F_{opt}) | G_{pe} | | 13 | | dB |
| | $V_{CE} = 2 V$, $I_C = 5 mA$, $Z_S = Z_{Sopt}$, $Z_L = 50 \Omega$ $f = 2 GHz$ | G_{pe} | | 11.5 | | dB |
| Transducer gain | $V_{CE} = 2 V$, $I_C = 5 mA$, $Z_0 = 50 \Omega$, $f = 2 GHz$ | $ S_{21e} ^2$ | | 12.5 | | dB |

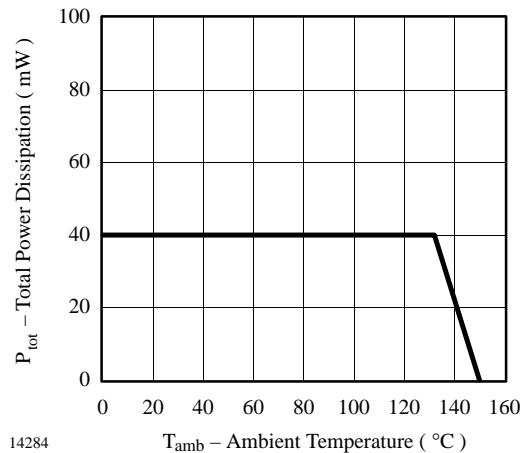
Typical Characteristics (T_{amb} = 25°C unless otherwise specified)


Figure 1. Total Power Dissipation vs. Ambient Temperature

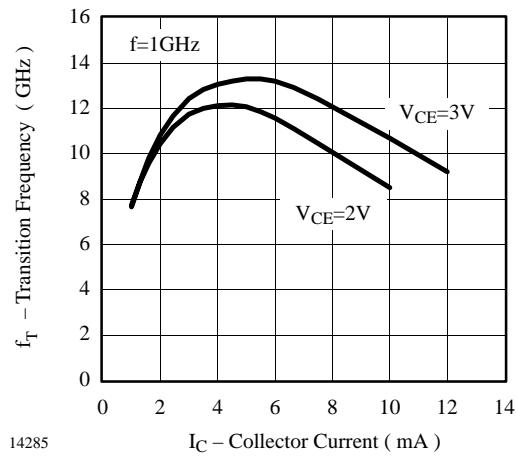


Figure 2. Transition Frequency vs. Collector Current

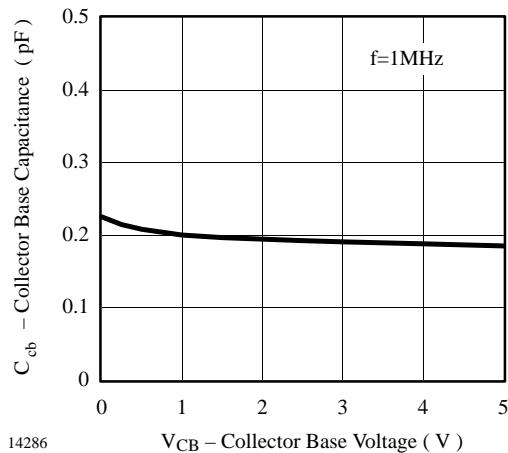


Figure 3. Collector Base Capacitance vs. Collector Base Voltage

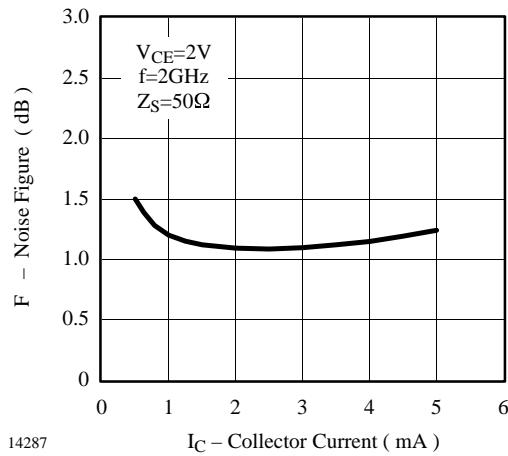
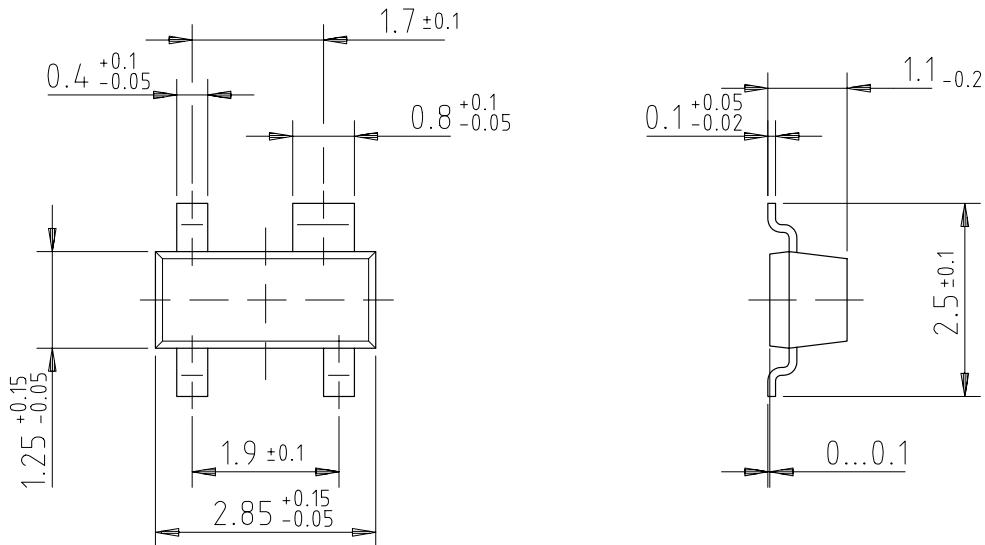
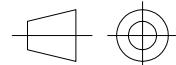
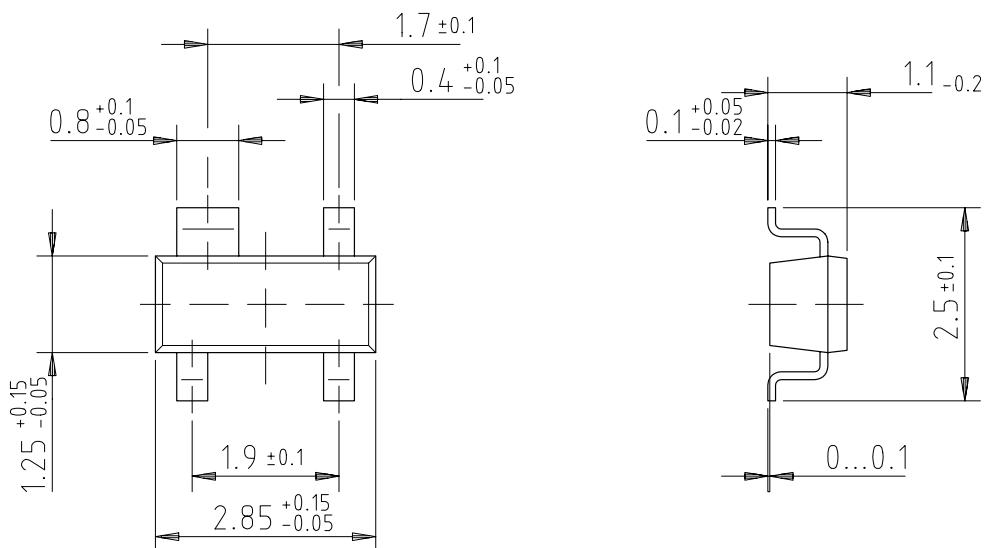


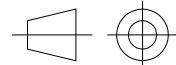
Figure 4. Noise Figure vs. Collector Current

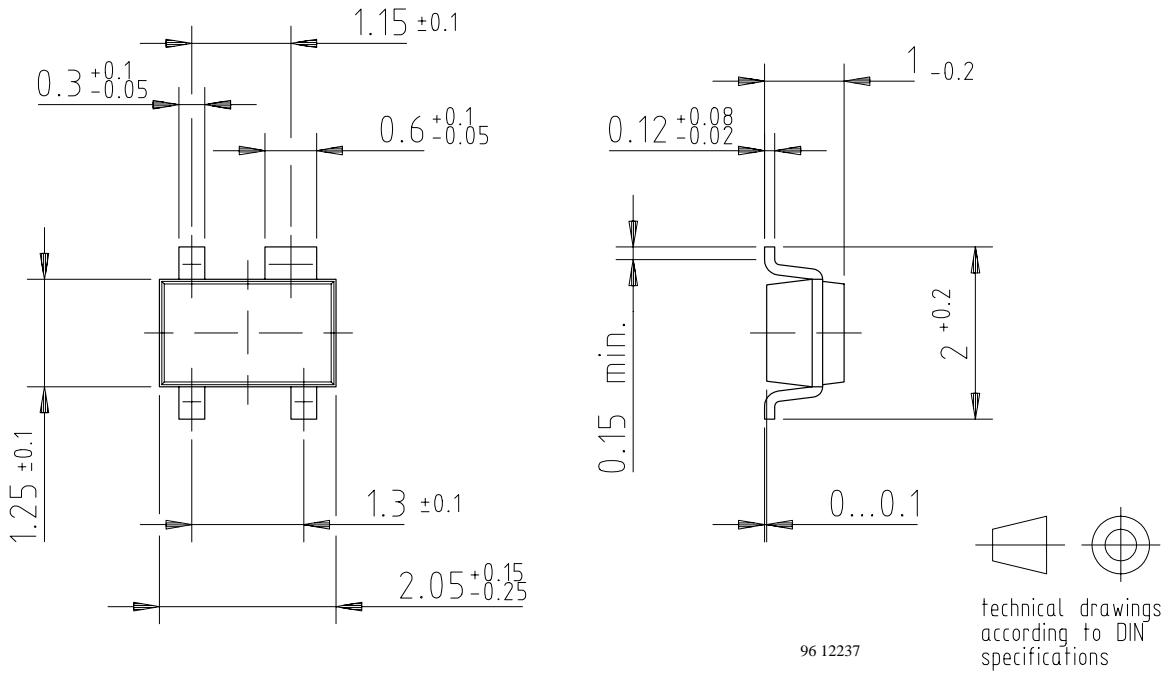
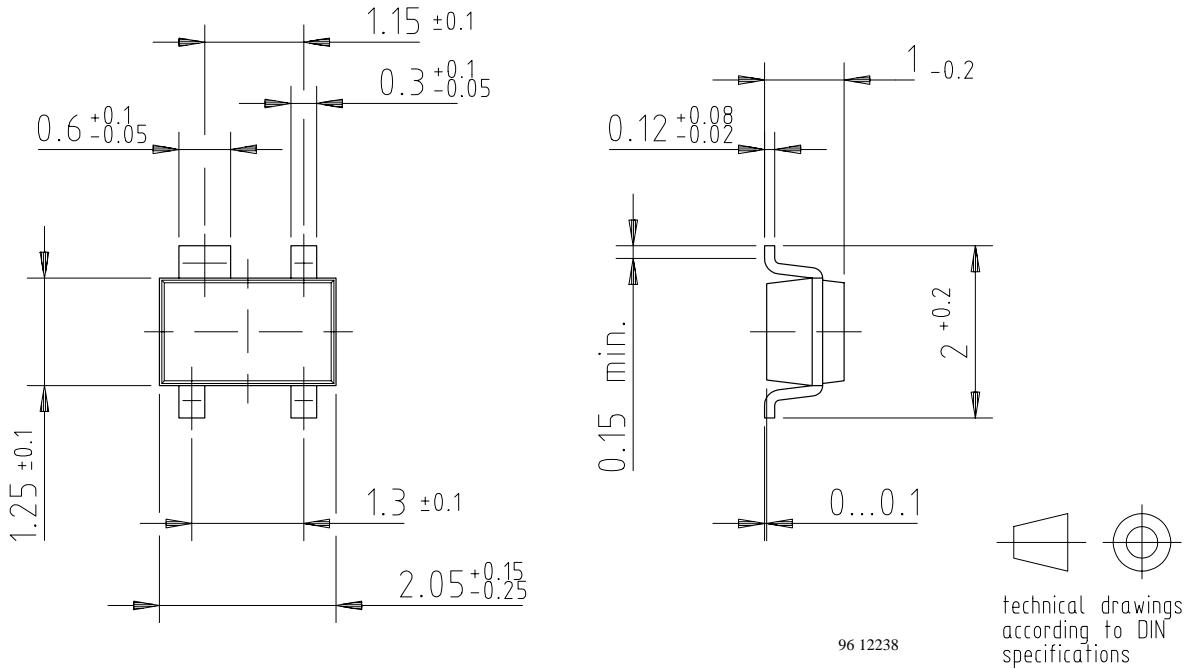
Dimensions of TSDF1205 in mm

96 12240

technical drawings
according to DIN
specifications**Dimensions of TSDF1205R in mm**

96 12239

technical drawings
according to DIN
specifications

Dimensions of TSDF1205W in mm

Dimensions of TSDF1205RW in mm


Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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